

## Refine Search

### Search Results -

Terms	Documents
L9	0

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
**IBM Technical Disclosure Bulletins**

Search:

L10

Recall Text

Clear

Refine Search

Interrupt

### Search History

DATE: Thursday, January 27, 2005    [Printable Copy](#)    [Create Case](#)

**Set Name Query**  
 side by side

**Hit Count Set Name**  
 result set

DB=TDBD; PLUR=YES; OP=OR

L10    L9

0    L10

DB=DWPI; PLUR=YES; OP=OR

L9    L8

0    L9

DB=JPAB; PLUR=YES; OP=OR

L8    L7

0    L8

DB=EPAB; PLUR=YES; OP=OR

L7    L6

0    L7

DB=USOC; PLUR=YES; OP=OR

L6    L5

0    L6

DB=PGPB; PLUR=YES; OP=OR

L5    L4

0    L5

DB=USPT; PLUR=YES; OP=OR

L4    L3 and leakage

1    L4

L3    L2 and "read transistor" and "storage transistor"

1    L3

<u>L2</u>	L1 and ("5 nanometers" near7 channel)	5	<u>L2</u>
<u>L1</u>	memory	480633	<u>L1</u>

END OF SEARCH HISTORY